# \*-ITN

# 1. The Periodic Building Unit (PBU)

The structure of \*- ITN is built from the layer shown in Figure 1 (a, b) which is built up by the building unit shown in (c and d).



Figure 1. The periodic building unit (PBU) building up the structure of \*-ITN is the layer Viewed along (a) [100] and (b) [010]. The PBU is a layer extending along the *a* and *b* directions. The layer is built from the building unit shown in (c) along [100] and (d) along [010].

# 2. Type of faulting:

Two basic types of disorder is present in the \*-ITN structure, 1-dimensional stacking disorder of the PBU's along [001] and twinning.

## 3. Connectivity patterns of the PBUs

The structure of \*-ITN allows two types of disorders, stacking disorder and twinning. The two can occur independent from each other.

### a) Stacking disorder viewed [100]

Neighboring PBUs can be connected along [001] with three different translations along *a*.

- a) The lateral translation of the top layer is 0 **b** with respect to the previous layer.
- b) The lateral translation of the top layer is 1/3 b with respect to the previous layer.
- c) The lateral translation of the top layer is -1/3 b with respect to the previous layer.



Figure 2. Connectivity of neighboring PBUs along [001] has three possibilities, via 6-6-4 – ring sequence (a) and 6-5-5 – ring sequence (b and c), respectively. View along [100]

#### b) Twinning in the projection along [010]

The PBU of \*-ITN allows a geometrically feasible connectivity along [001] also after the PBU is mirrored perpendicular to [100]. This gives rise to twinning in the structure.



Figure 3. The bottom layer is identical in (a) and (b), the top layer in (b) is mirrored perpendicular to [100]. They PBU can still be connected along [001] with good geometry. View along [010].

#### 4. Ordered end-members

The simplest ordered end-members in the \*-ITN family are given below in Table 1 and in Figure 3. Polymorph A is built from alternating translations of +1/3b and -1/3b. None of them has been observed yet as ordered material.

	Polymorph	Lateral shifts between subsequent PBU stacked along	Space group
		[001]; Shifts are given in fractions of <b>b</b>	
	А	(+1/3); (-1/3); (+1/3);	P2/c
	В	(+1/3); (+1/3); or (-1/3); (-1/3);	<i>P</i> -1
	С	(0); (0);	P2/m

Table 1. Stacking sequences of PBU for the simplest ordered end-members in the \*-ITN family.



a

Figure 4. The structures of the three ordered polymorphs A (a), B (b) and C (c), described in the Table 1 viewed along [100].

## 5. Disordered materials with \*-ITN structure synthesized so far:

Two materials have been synthesized so far with XRPD patterns consistent with the \*-ITN structure: ITQ-39<sup>1, 2, 3</sup> and SSZ-83<sup>4</sup>.

## 6. Supplementary Material

Simulation of XRPD patterns for \*-ITN family. The simulations below shows the intergrowth between polymorph A and polymorph B as described in Table 1. The content of polymorph C as well as the effects of small twin domains are not considered in these simulations.



Figure 5. Simulated XRPD patterns with the intensity (a.u.) versus diffraction angle (2 $\theta$ ) of the intergrowth between polymorph A and polymorph B of the \*-ITN family in steps of 20% intergrowth. The simulations were performed with the software DIFFaX<sup>5</sup>.

## 7. References

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